Ion implantation range data for silicon and germanium device technologies

Learned Information (Europe) Ltd. - ION IMPLANTATION OF SILICON AND GERMANIUM AT ROOM TEMPERATURE. ANALYSIS BY MEANS OF 1.0

Description: -
-
Trieste (Italy : Province) -- Social life and customs.
Trieste (Italy) -- Social life and customs.
Friuli-Venezia Giulia (Italy) -- Social life and customs.
Cookery, Italian.
Ion implanatation -- Tables.Ion implantation range data for silicon and germanium device technologies
-Ion implantation range data for silicon and germanium device technologies
Notes: Includes bibliographical references.
This edition was published in 1978

Tags: #ION #IMPLANTATION #OF #SILICON #AND #GERMANIUM #AT #ROOM #TEMPERATURE. #ANALYSIS #BY #MEANS #OF #1.0

ION IMPLANTATION OF SILICON AND GERMANIUM AT ROOM TEMPERATURE. ANALYSIS BY MEANS OF 1.0

The structural change caused by the implantation produces a surface compression in the steel, which prevents crack propagation and thus makes the material more resistant to fracture. The loss of ion energy in the target is called and can be simulated with the method. Toshiba Corp Original Assignee Toshiba Corp Priority date The priority date is an assumption and is not a legal conclusion.

Table III from Modeling of boron and phosphorus implantation into (100) Germanium

The polycrystalline silicon layer 22 acts as the gate electrode of the MOSFET 10, while the underlying thermal oxide thin-film 18 functions as a gate insulation layer.

US5272365A

Thus, ion implantation is especially useful in cases where the chemical or structural change is desired to be near the surface of the target. With such an arrangement, stray or parasitic capacitance generated between the gate electrode 92 and the remaining components of the MOSFET 90 are decreased, thereby to improve the characteristics thereof.

Ion Implantation

HEMT ; with two-dimensional charge-carrier layer formed at a heterojunction interface with confinement of carriers by at least two heterojunctions, e. Please note the Image in this listing is a stock photo and may not match the covers of the actual item,750grams, ISBN:0904933083, VNU Business Publishing Ltd, 1978 Bernard Smith: Ion Implantation Range Data for Silicon and Germanium Device Technologies - hardcover 1978, ISBN: VNU Business Publishing Ltd, 1978.

Table III from Modeling of boron and phosphorus implantation into (100) Germanium

With the MOSFET 50, it becomes possible to eliminate the generation of undesirable current leakage in the junction section between the the substrate 52 and the source layer 54 and the one between the substrate 52 and the drain layer 56. The effect is only appreciable for very large doses. Materials Science and Engineering: A.

Ion implantation

Ion implantation is used in and in metal finishing, as well as in research. This book has hardback covers. Such temperature value will range from 500 to 800 degrees.

Related Books

- Madre Itàlia - made in Italy : il purismo di ieri, le paure di oggi, gli auspici futuri
- Intellectuels et Etat au Mexique au XXe siècle
- Family Chumash - introductions, translations, and concise commentary with haftarahs
- Agricultural transition in Central and Eastern Europe and the former U.S.S.R.
- Woodstock, Millville, and Coldstream Map-Areas, Caleton and York Counties, New Brunswick.